



**EECS 151/251A**  
**Spring 2021**  
**Digital Design and**  
**Integrated Circuits**

Instructors:  
Wawrzynek

**Lecture 10: CMOS2**

# *Announcements*

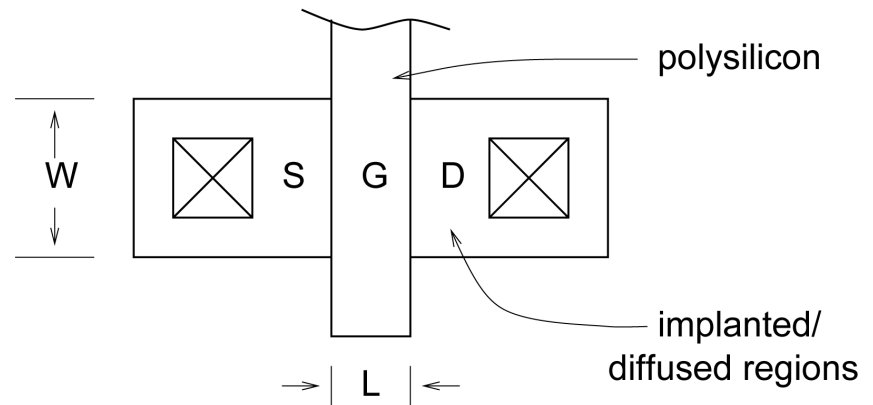
- ❑ Virtual Front Row for today 2/18:
  - ❑ Jose Rodriguez
  - ❑ Khashayar Pirouzmand
  - ❑ Jiefeng Chen
  - ❑ Rajiv Govindjee
  - ❑ James Shi
- ❑ **Questions/comments used in class participation points.**
- ❑ Homework assignment 4 due Monday. Start early, challenging!



## CMOS Transistors

# Transistor Strength and Symmetry

1. Transistor “strength” proportional to  $W/L$ . In digital circuits,  $L$  is almost always minimal allowed by process.



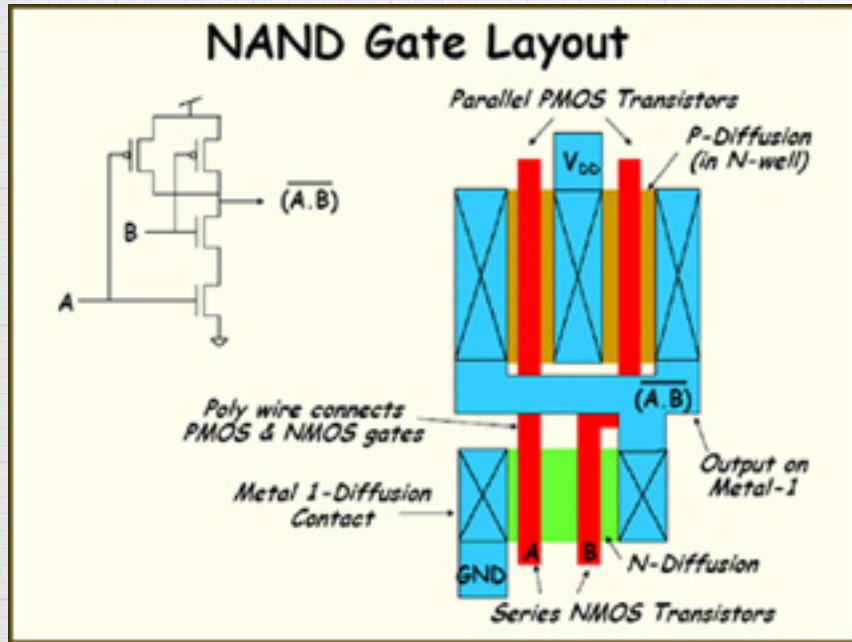
2. MOS transistors are symmetrical devices (Source and drain are interchangeable). But usually designed to be used in one direction.

For nFET, source is the node w/ the lowest voltage. For pFET source is node with highest voltage.



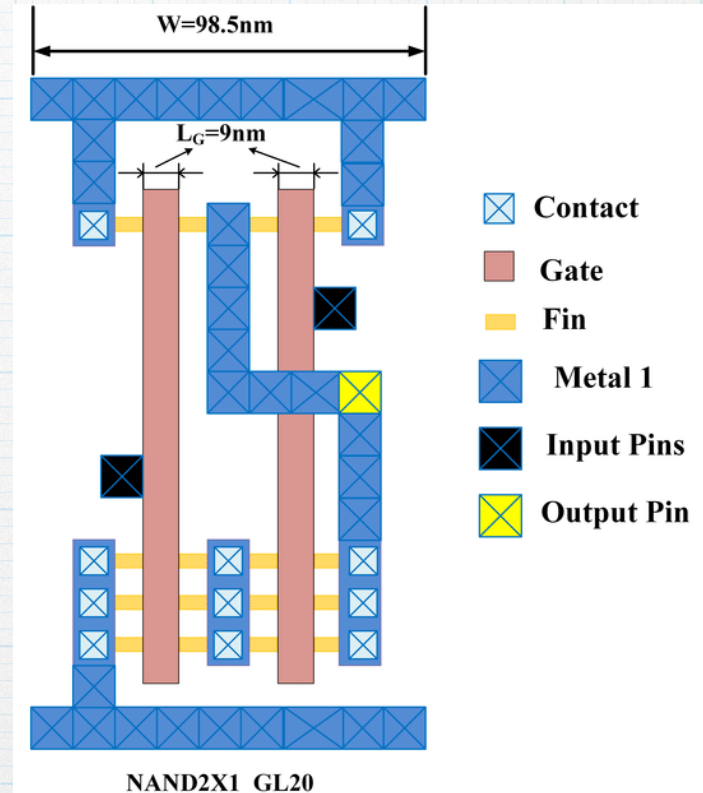
# Circuit Layout Examples

## ► 2-input NAND



NAND gate layout from Lecture 3: CMOS Technology and Logic Gates. (Image by Professors Arvind and Asanovic.)

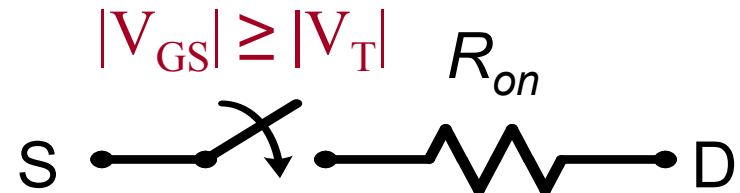
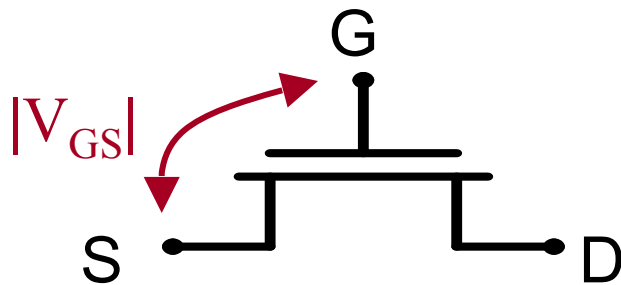
## Finfet layout



from Ji Li

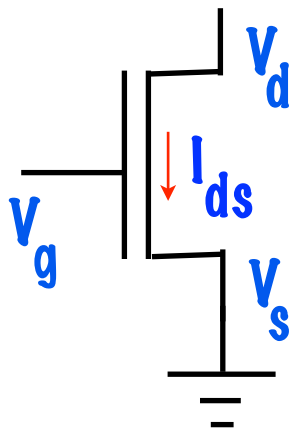
# MOS Transistor as a Resistive Switch

MOS Transistor  $\longleftrightarrow$  A Switch!

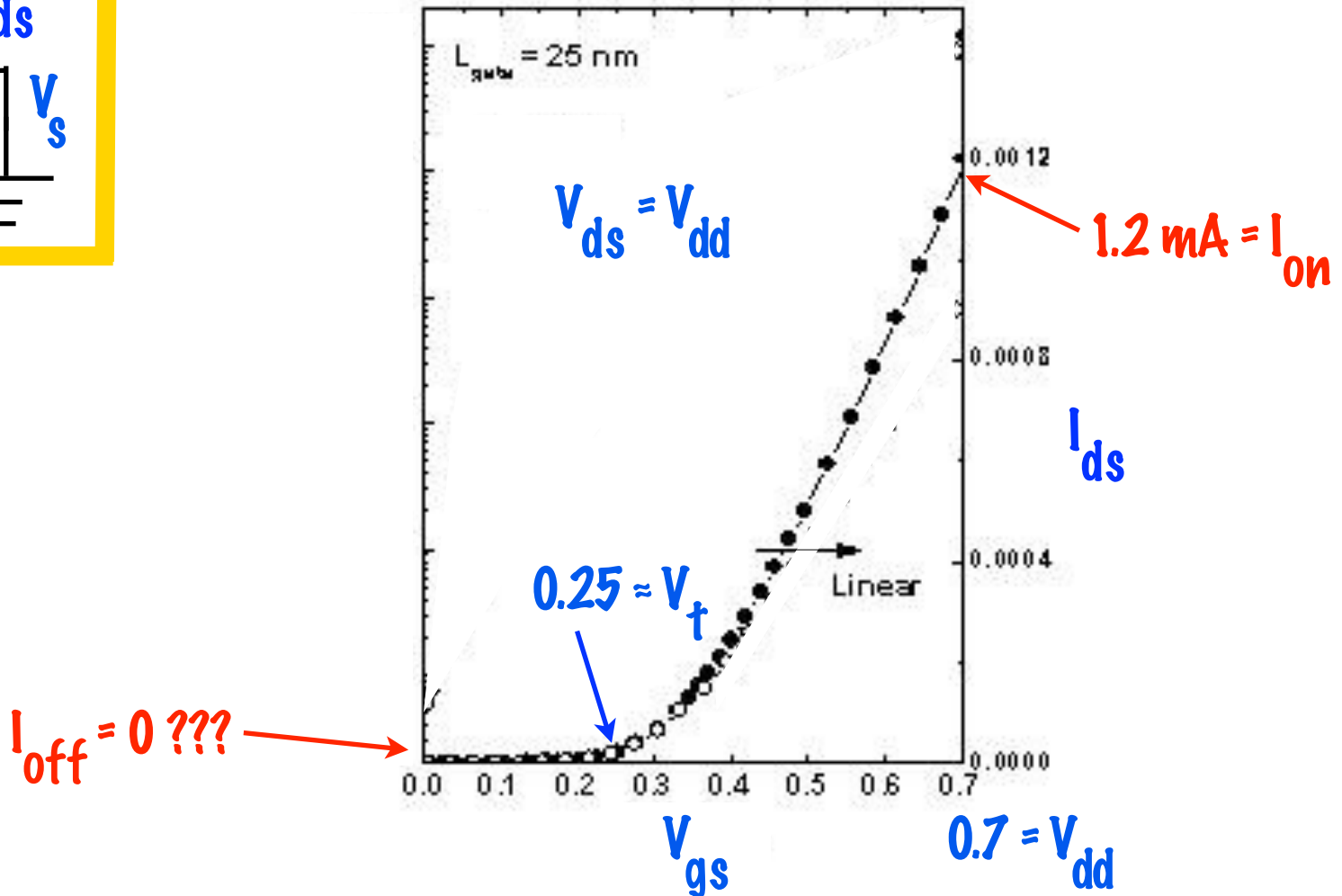


*Let's look beneath the abstraction:  
origins of  $V_T$  and  $R_{on}$*

# MOSFET Threshold Voltage

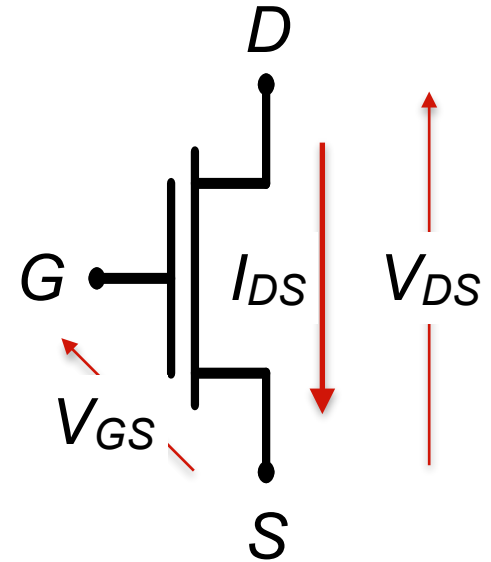
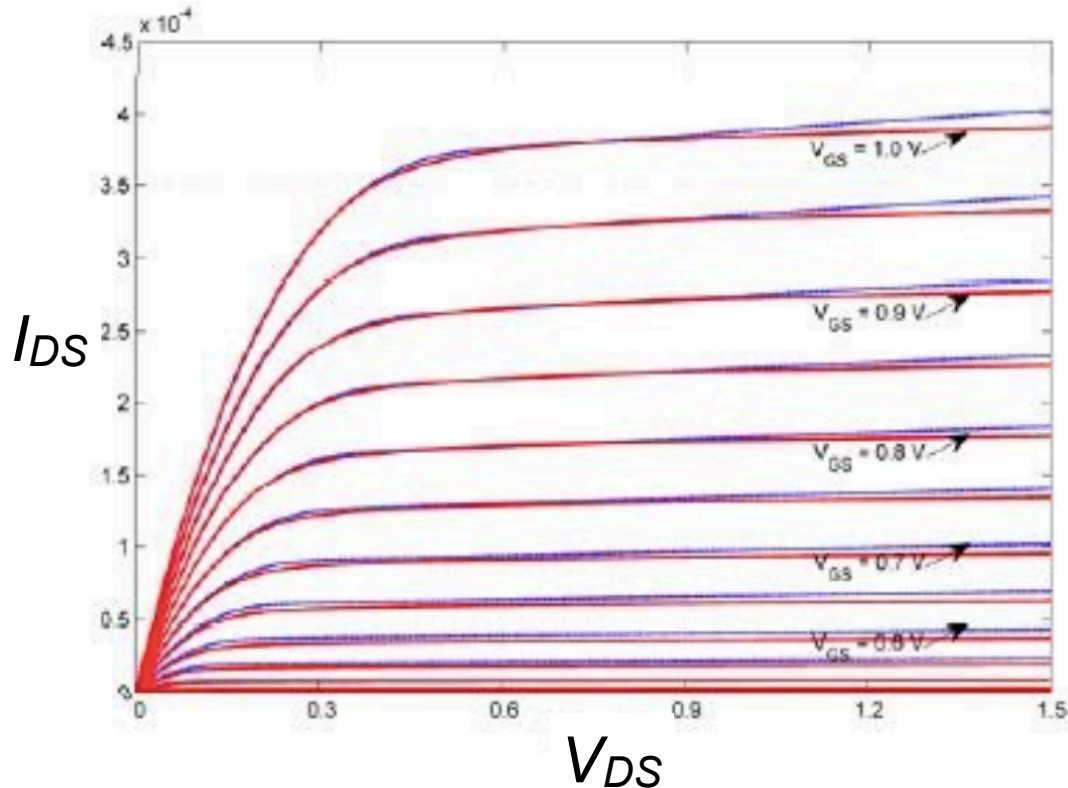


Transistor "turns on" when  $V_{gs}$  is  $> V_t$ .



# Transistor “resistance”

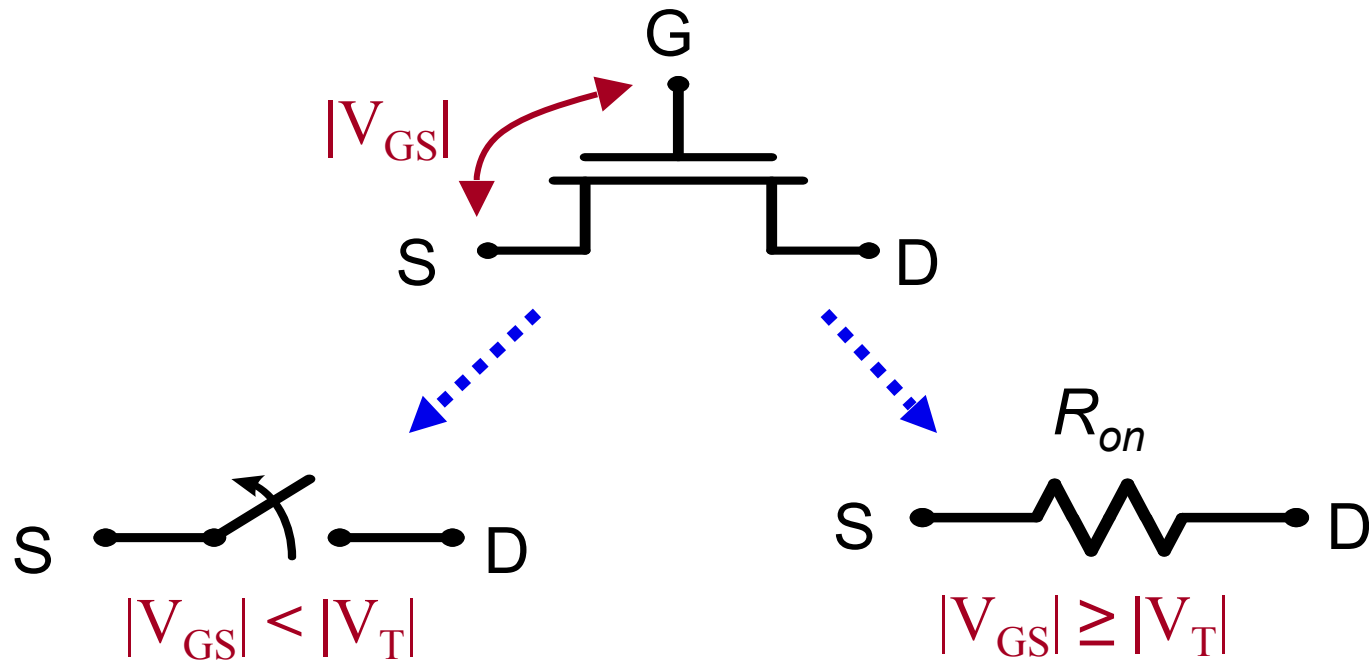
- Nonlinear I/V characteristic:



- But, linearizing makes all delay and power calculations simple (usually just 1st order ODEs):



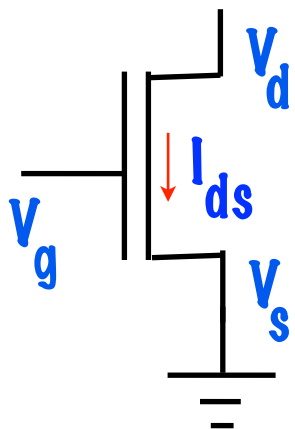
# ON/OFF Switch Model of MOS Transistor



# Plot on a "Log" Scale to See "Off" Current

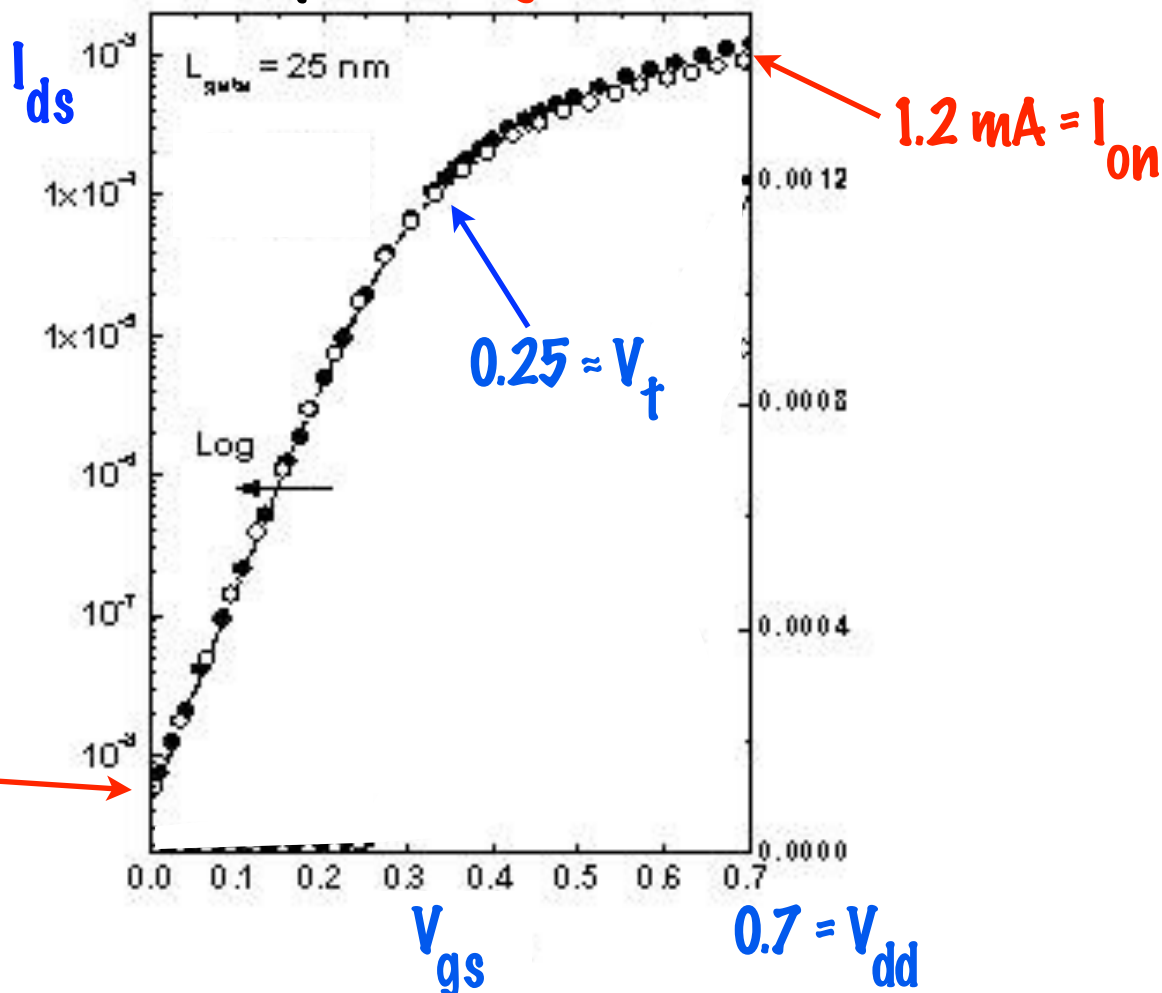
Process engineers can:

increase  $I_{on}$  by lowering  $V_t$  - but that raises  $I_{off}$   
decrease  $I_{off}$  by raising  $V_t$  - but that lowers  $I_{on}$ .

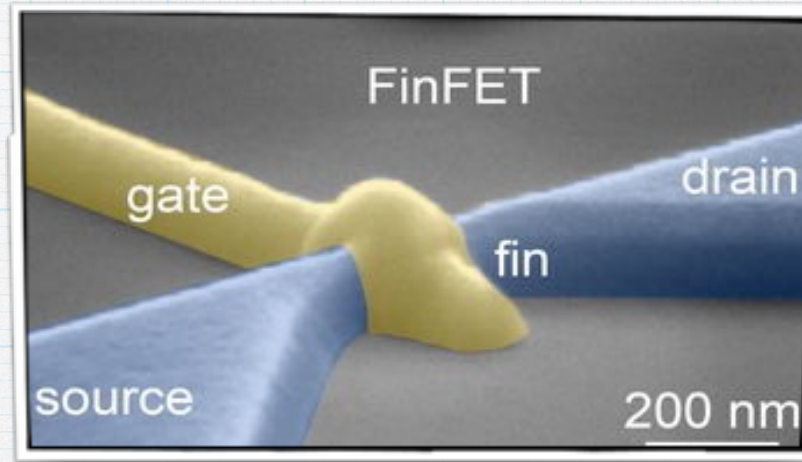


$$V_{ds} = V_{dd}$$

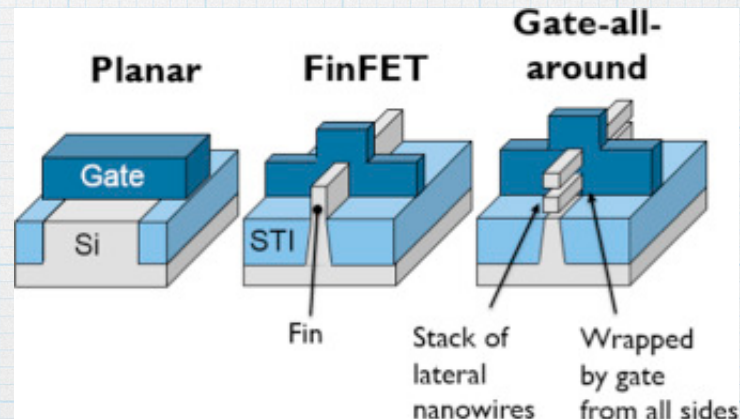
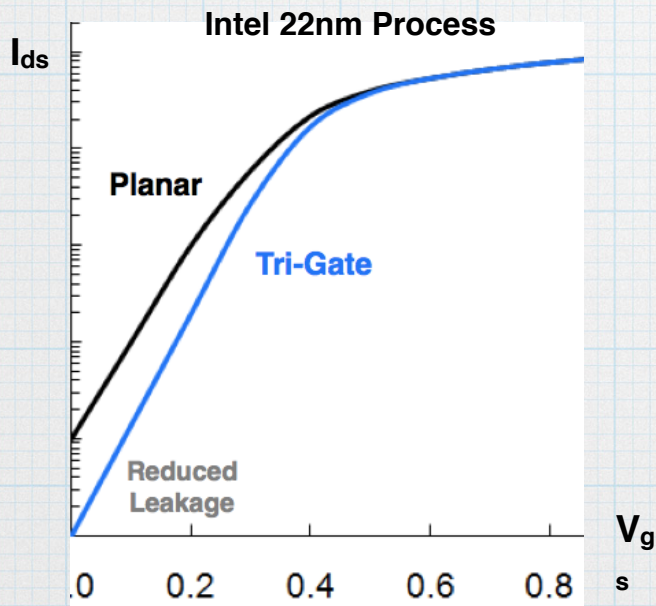
$$I_{off} \approx 10 \text{ nA}$$



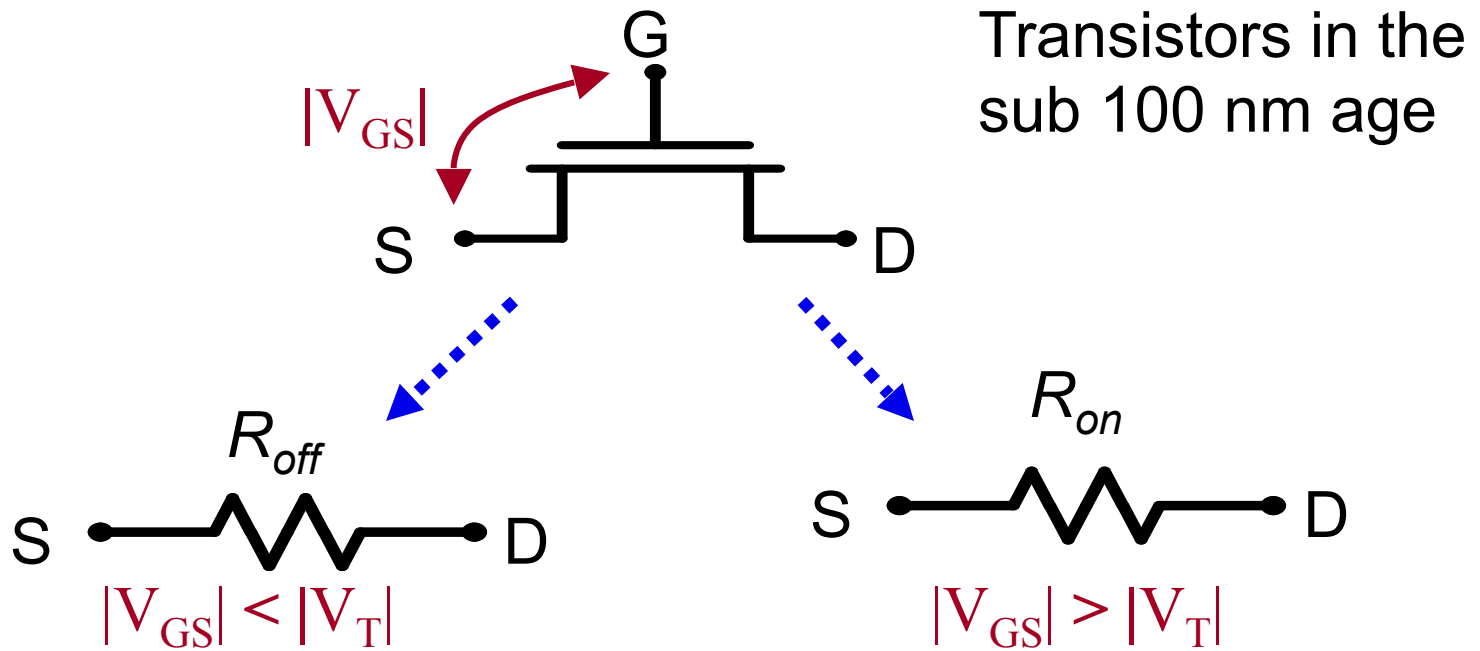
# Latest Modern Process



Transistor channel is a raised fin.  
Gate controls channel from sides and top.

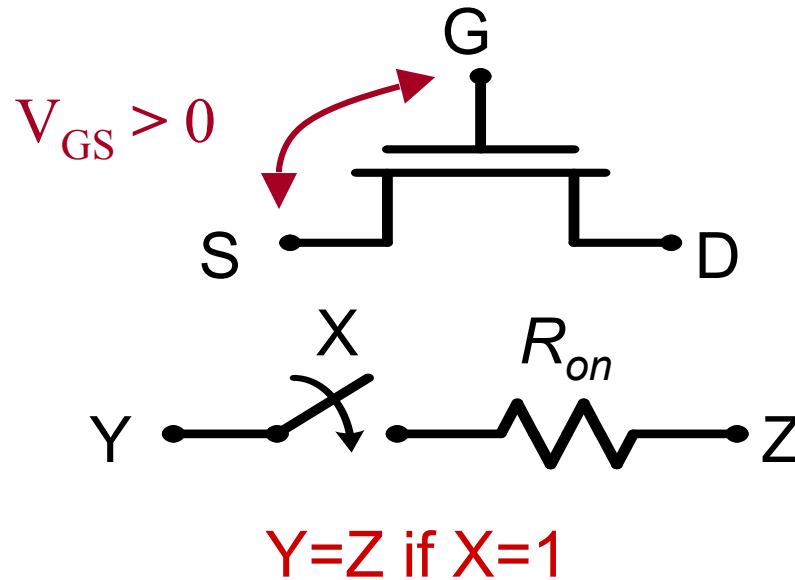


# A More Realistic Switch



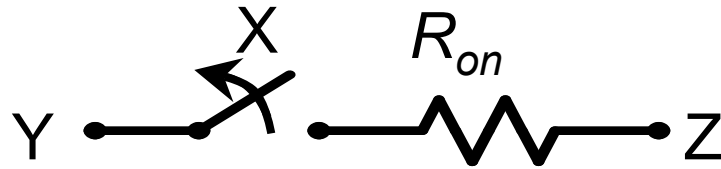
# A Logic Perspective

## NMOS Transistor



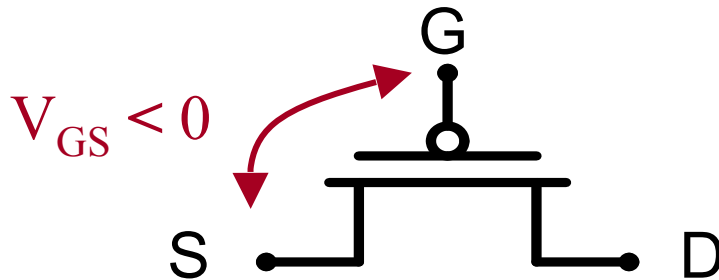


# A Complementary Switch



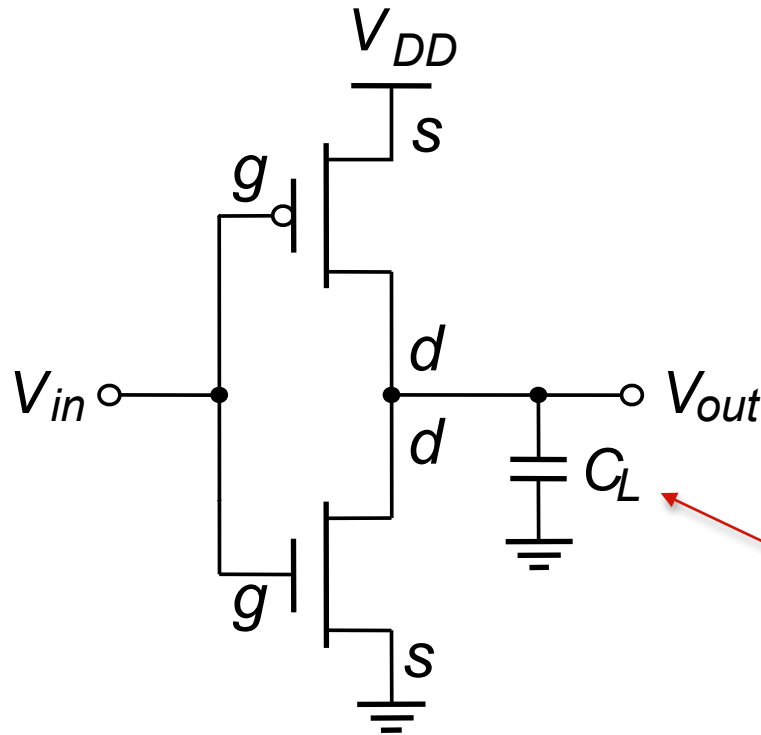
$Y=Z$  if  $X=0$

## PMOS Transistor



*Remember, source is the node w/ the highest voltage.*

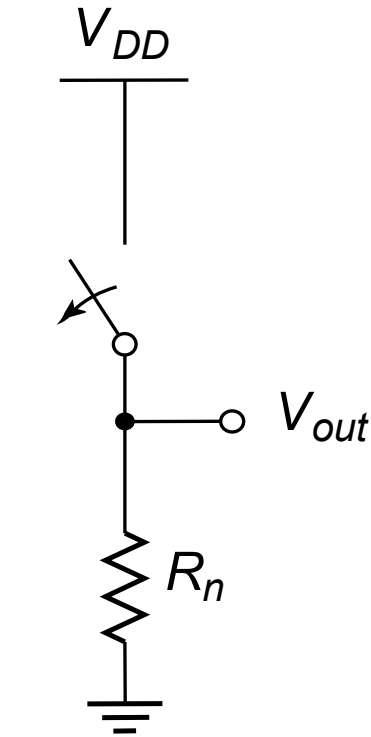
# The CMOS Inverter: A First Glance



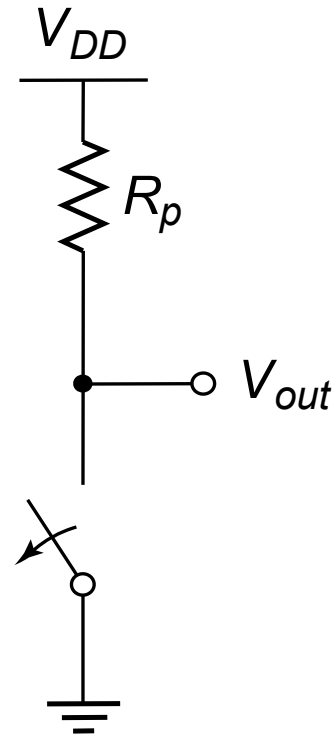
*Represents the sum of all the capacitance at the output of the inverter and everything to which it connects: (drains, interconnections gate capacitance of next gate(s))*

# The Switch Inverter

## First-Order DC Analysis\*



$$V_{in} = V_{DD}$$



$$V_{in} = 0$$

$$V_{OL} = 0$$
$$V_{OH} = V_{DD}$$

\*First-order means we will ignore Capacitance.

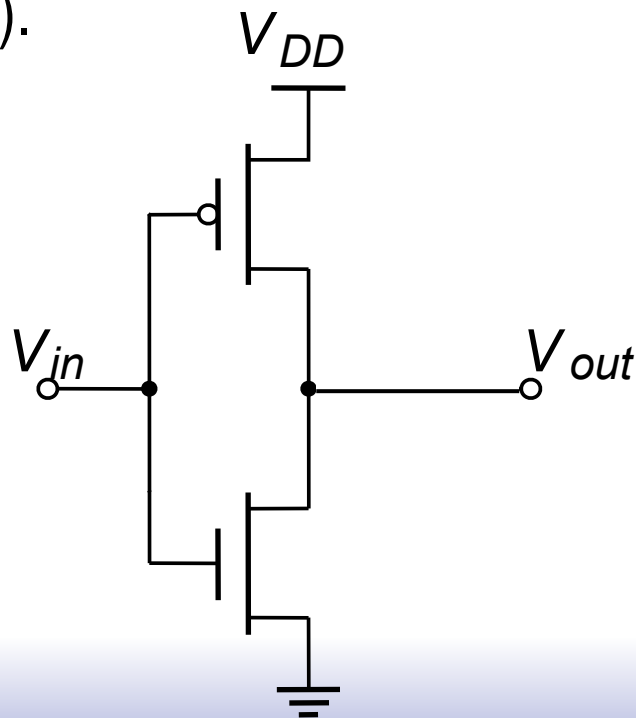


**Switch logic**

# Static Logic Gate

- At every point in time (except during the switching transients) each gate output is connected to either  $V_{DD}$  or  $V_{GND}$  via a low resistive path.
- The output of the gate assumes at all times the value of the Boolean function implemented by the circuit (ignoring, once again, the transient effects during switching periods).

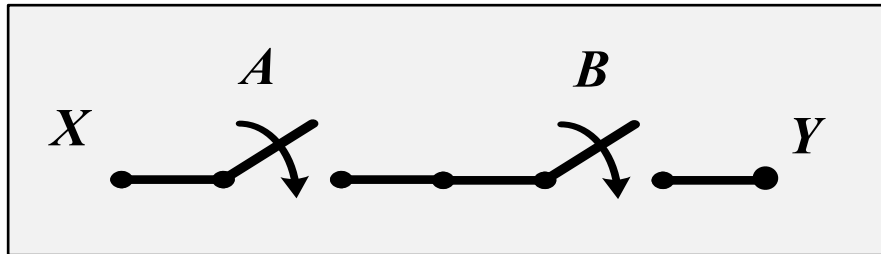
Example: CMOS Inverter





# Building logic from switches (NMOS)

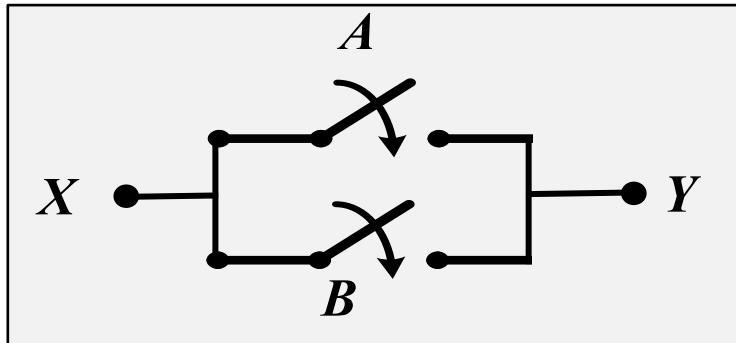
**Series**



**AND**

**$Y = X$  if  $A$  AND  $B$**

**Parallel**



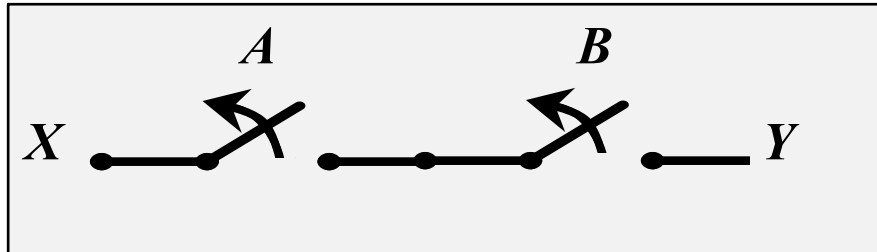
**OR**

**$Y = X$  if  $A$  OR  $B$**

(output undefined if condition not true)

# Logic using inverting switches (PMOS)

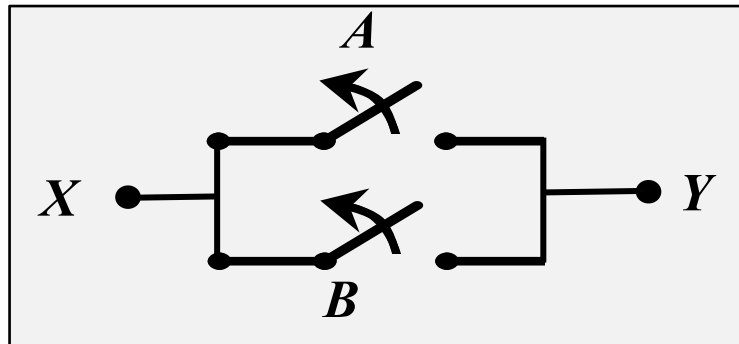
**Series**



**NOR**

$$Y = X \text{ if } \bar{A} \text{ AND } \bar{B} \\ = \overline{A + B}$$

**Parallel**



**NAND**

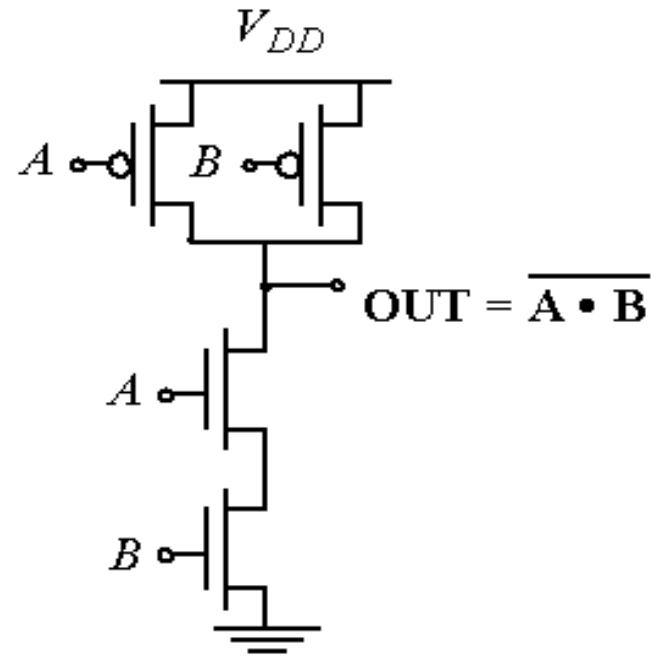
$$Y = X \text{ if } \bar{A} \text{ OR } \bar{B} \\ = \overline{AB}$$

(output undefined if condition not true)

# Example Gate: NAND

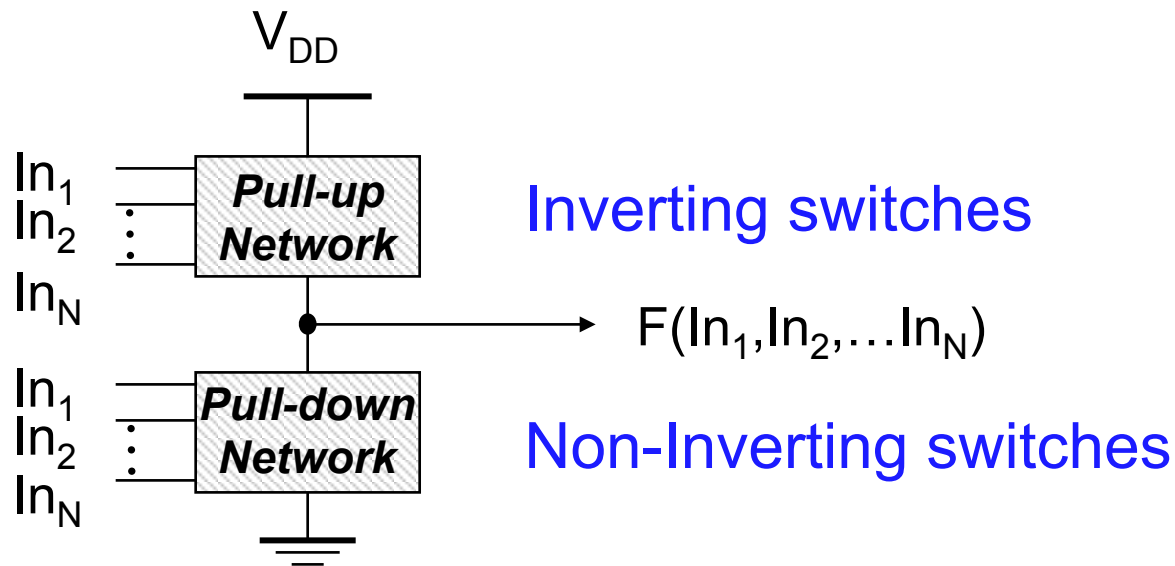
A	B	Out
0	0	1
0	1	1
1	0	1
1	1	0

**Truth Table of a 2 input NAND gate**



- PDN:  $G = AB \Rightarrow$  Conduction to GND
- PUN:  $F = \overline{A} + \overline{B} = \overline{AB} \Rightarrow$  Conduction to  $V_{DD}$

# Static Complementary CMOS



**PUN and PDN are dual logic networks:**

series connections in the PUN are parallel connections in the PDN  
parallel connections in the PUN are series connections in the PDN

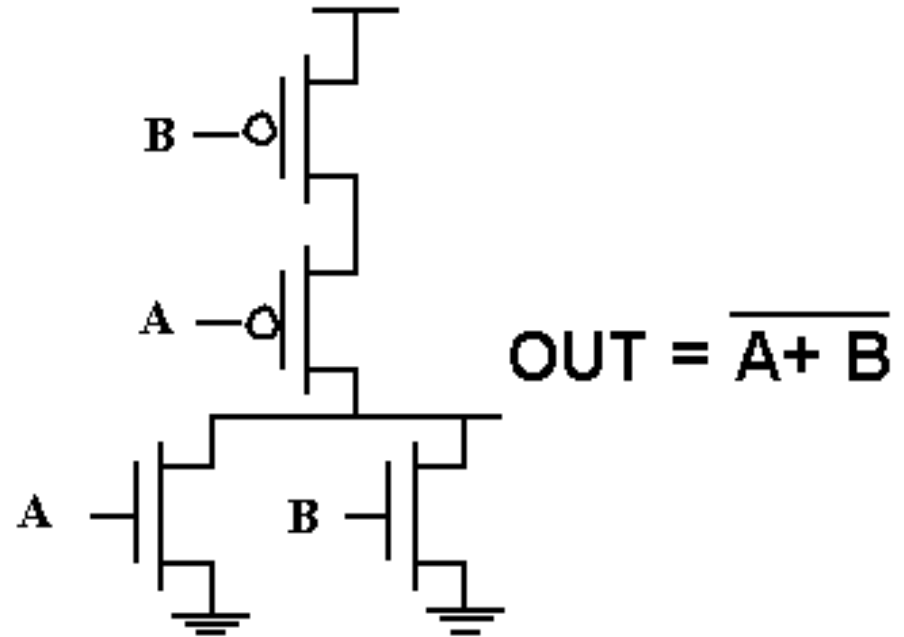
**PUN and PDN functions are complements:**

guarantees they are mutually exclusive, under all input values,  
one or the other is conductive, but never both!

# Example Gate: NOR

A	B	Out
0	0	1
0	1	0
1	0	0
1	1	0

Truth Table of a 2 input NOR gate

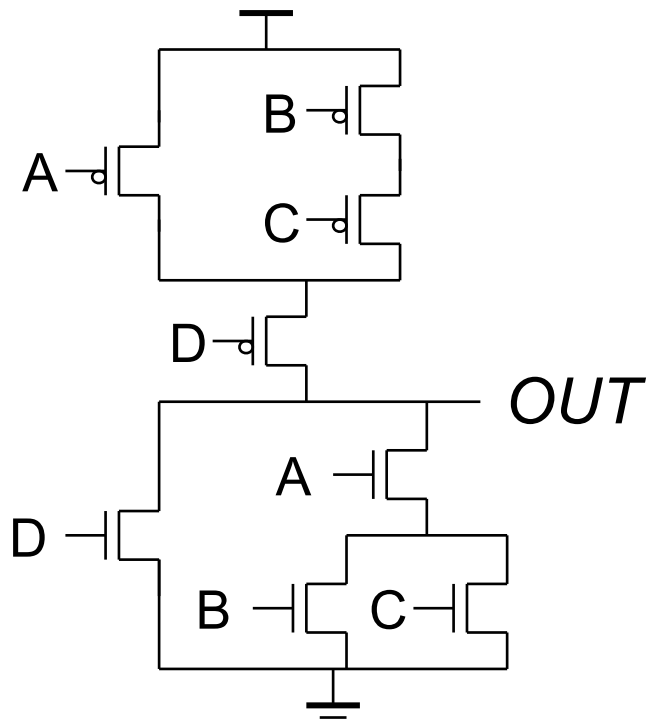




# Complex CMOS Gate

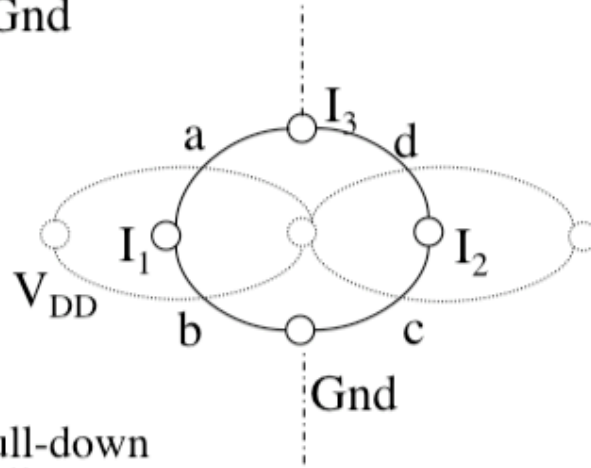
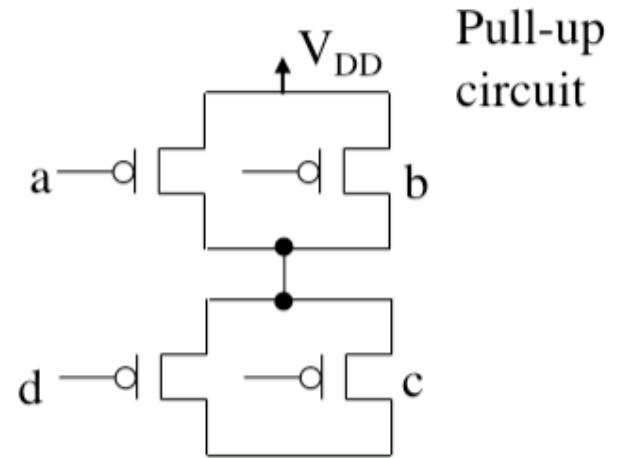
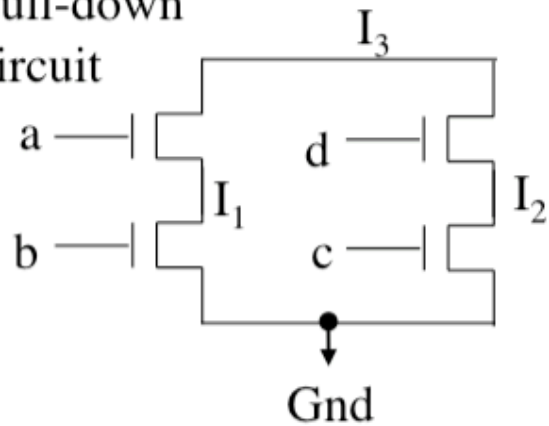
$$\overline{OUT} = \overline{D + A \cdot (B + C)}$$

$$OUT = \overline{D \cdot A + B \cdot C}$$



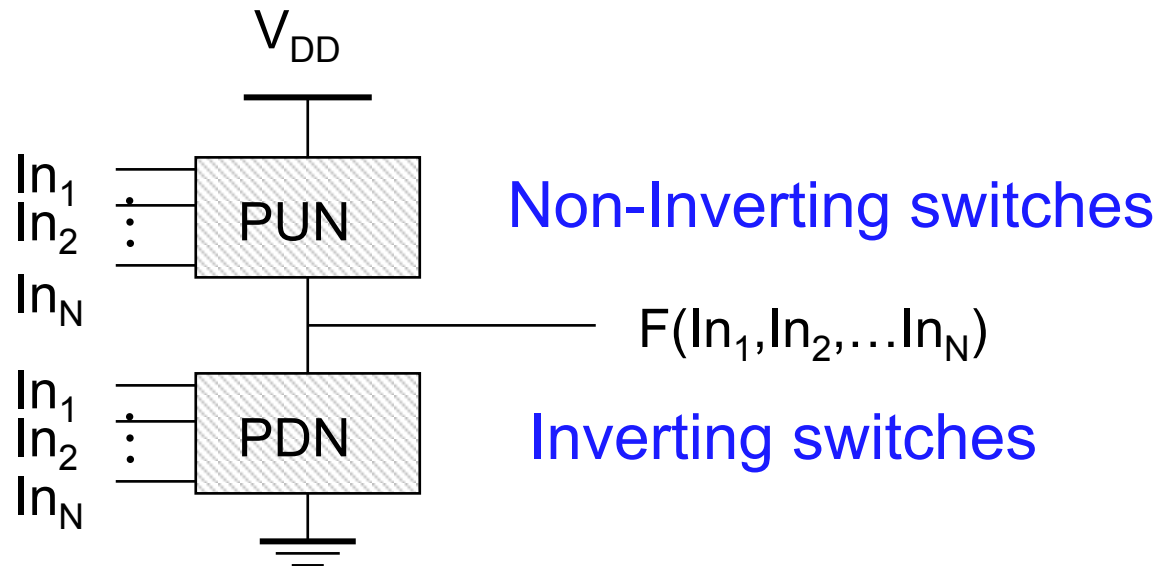
# Graph Models for Duals

Pull-down circuit



— Pull-down  
 ..... Pull-up

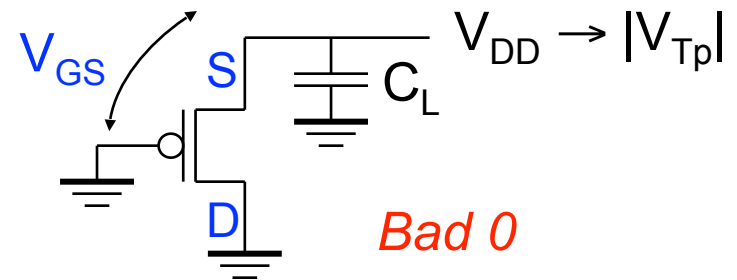
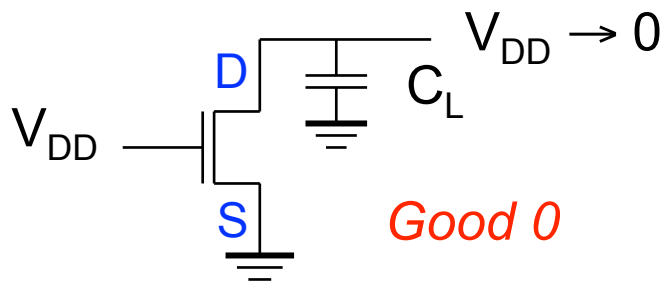
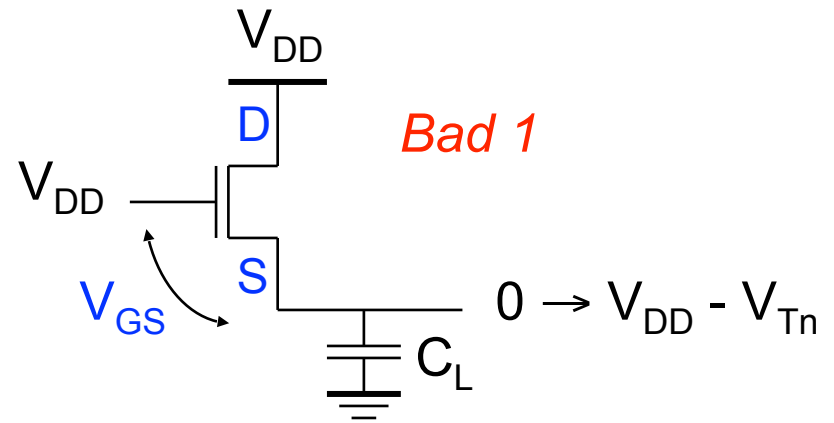
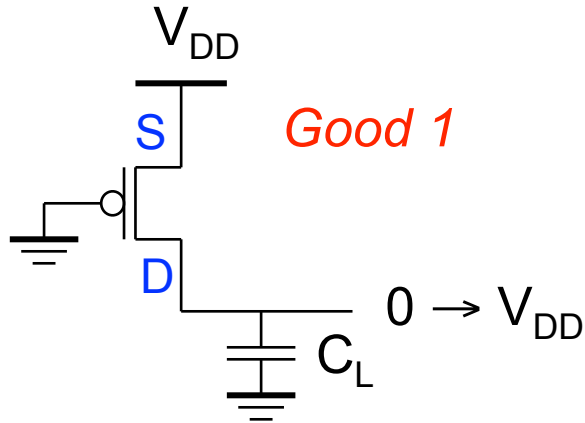
# Non-inverting logic



*Why is this  
a bad idea?*

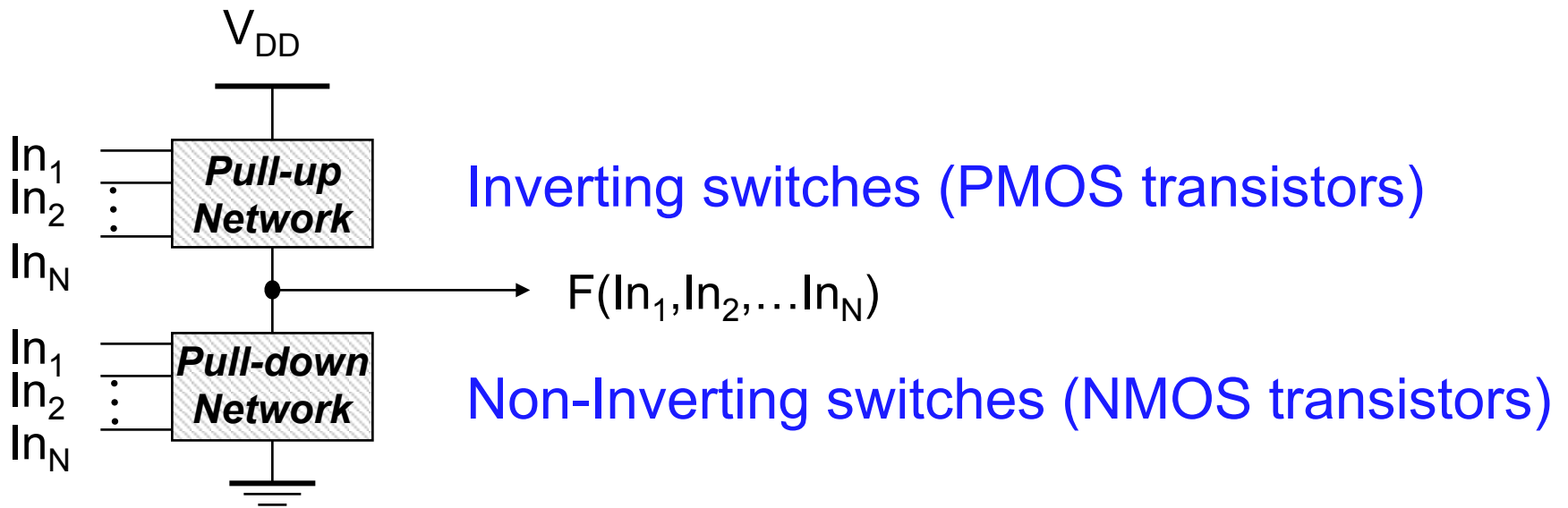
PUN and PDN are **dual** logic networks  
PUN and PDN functions are **complementary**

# Switch Limitations

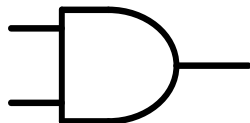


Tough luck ...

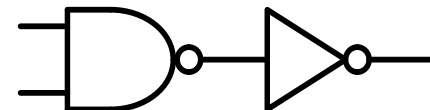
# “Static” CMOS gates



- ❑ Static CMOS gates are always inverting

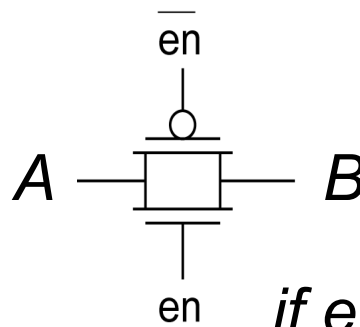


**AND = NAND + INV**



# Transmission Gate

- ❑ Transmission gates are the way to build ideal “switches” in CMOS.
- ❑ In general, for an ideal switch, both transistor types are needed:
  - ❑ nFET to pass zeros.
  - ❑ pFET to pass ones.
- ❑ The transmission gate is bi-directional (unlike logic gates).



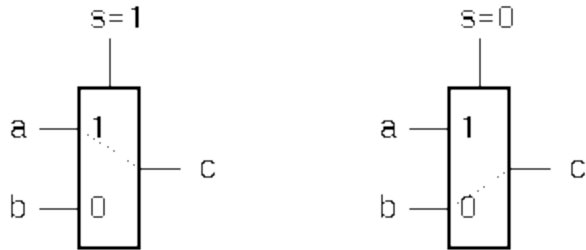
*if  $en == 1$  then  $A$  connects to  $B$*

- ❑ Does not directly connect to Vdd and GND, but can be combined with logic gates or buffers to simplify many logic structures.

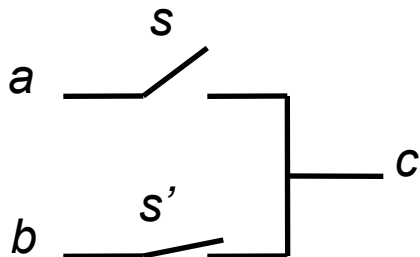
# Transmission-gate Multiplexor

2-to-1 multiplexor:

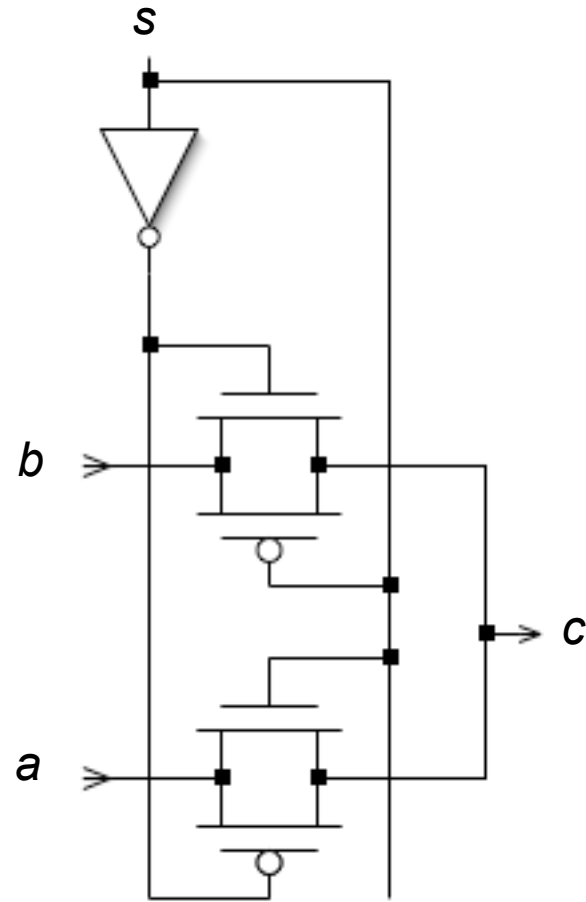
$$c = sa + s'b$$



Switches simplify the implementation:

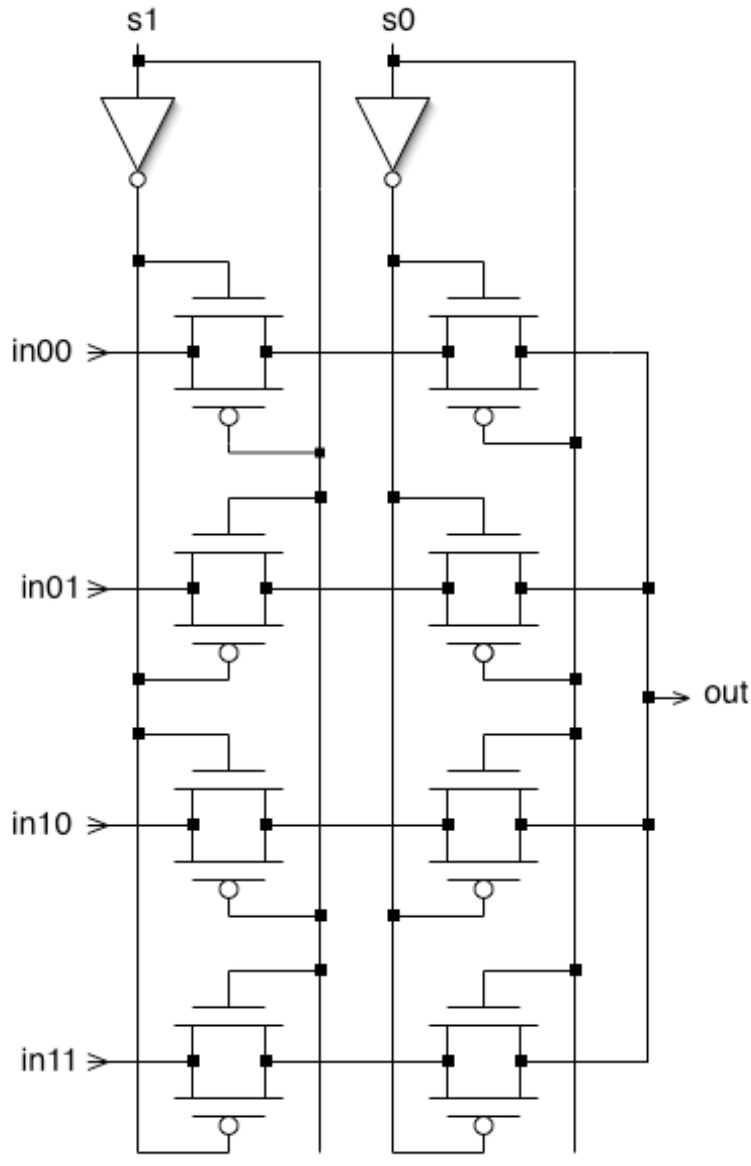


Compare the cost to logic gate implementation.



Care must be taken to not string together many pass-transistor stages. Occasionally, need to “rebuffer” with static gate.

# 4-to-1 Transmission-gate Mux



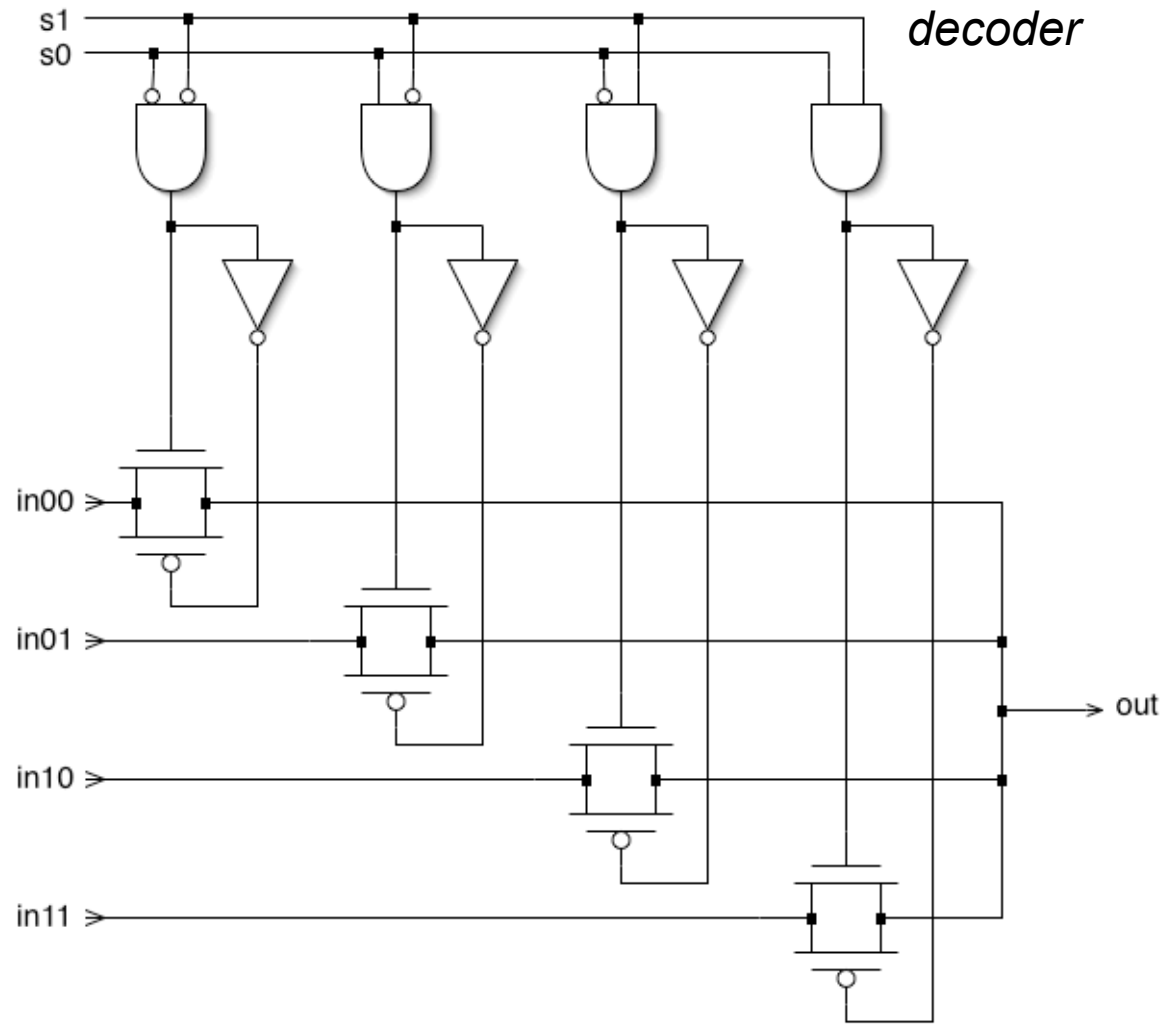
- The series connection of pass-transistors in each branch effectively forms the AND of  $s_1$  and  $s_0$  (or their complement).
- Compare cost to logic gate implementation

*Any alternate solutions?*



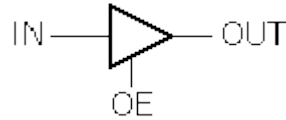
# Alternative 4-to-1 Multiplexor

- This version has less delay from in to out.
- In both versions, care must be taken to avoid turning on multiple paths simultaneously (shorting together the inputs).



# Tri-state Buffers

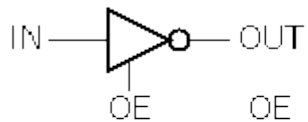
Tri-state Buffer:



OE	IN	OUT
0	0	Z
0	1	Z
1	0	0
1	1	1

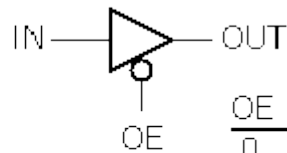
“high impedance” (output disconnected)

## Variations:



OE	IN	OUT
0	-	Z
1	0	1
1	1	0

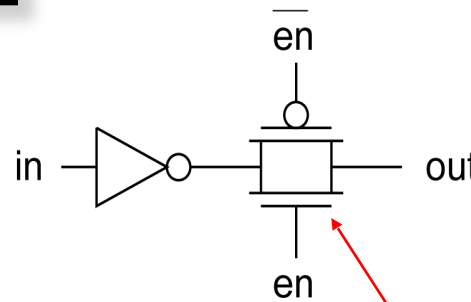
Inverting buffer



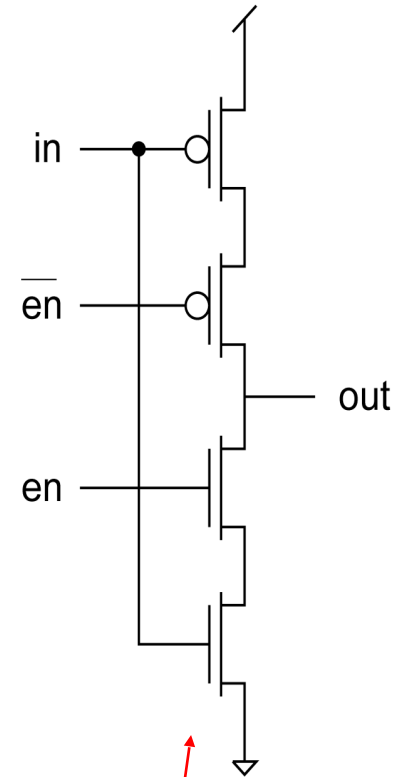
OE	IN	OUT
0	0	0
0	1	1
1	-	Z

Inverted enable

## CMOS Implementation

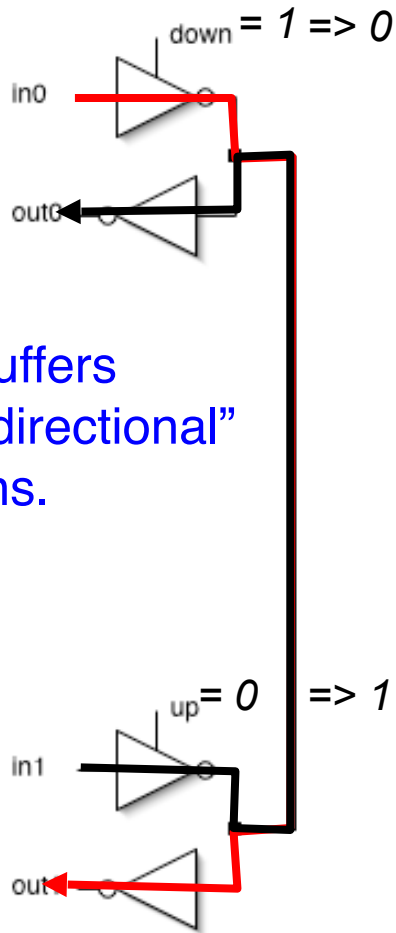


transmission gate provide the isolation:  
usually designed this way

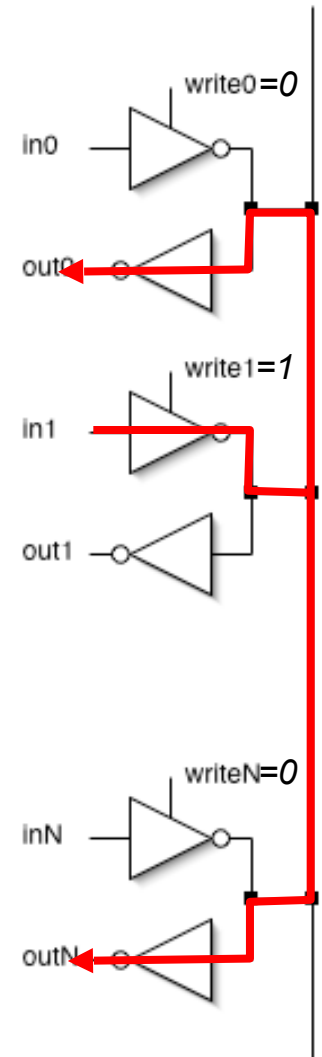


# Tri-state Buffers

Tri-state buffers enable “bidirectional” connections.

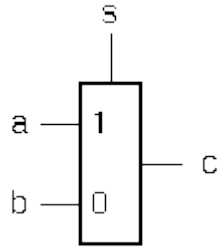


Tri-state buffers are used when multiple circuits all connect to a common node or wire. Only one circuit at a time is allowed to drive the bus. All others “disconnect” their outputs, but can “listen”.

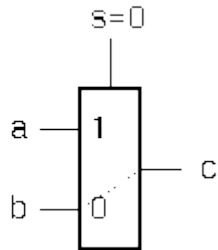
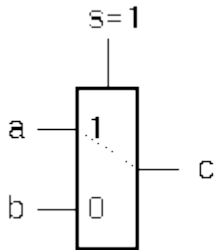


# Tri-state Based Multiplexor

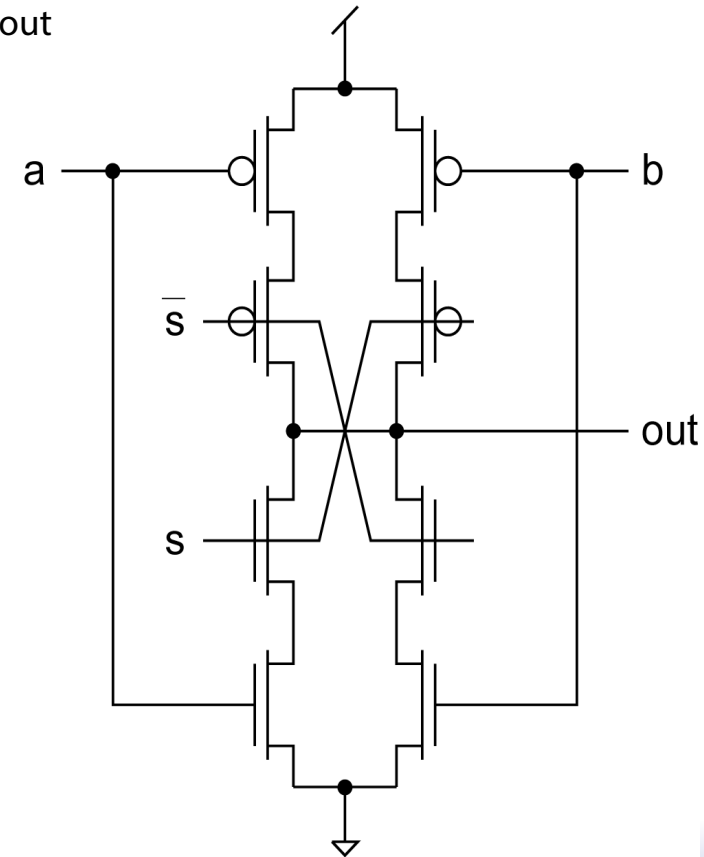
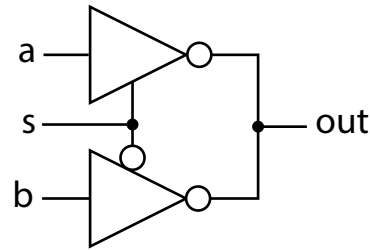
Multiplexor:



If  $s=1$  then  $c=a$  else  $c=b$

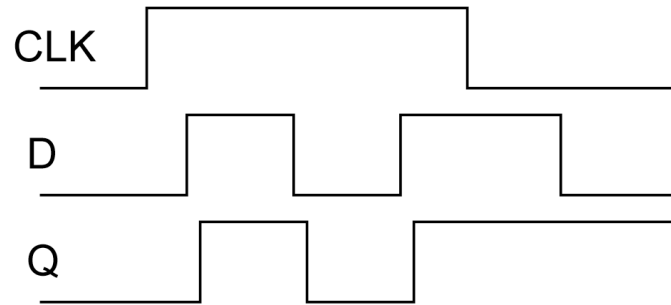
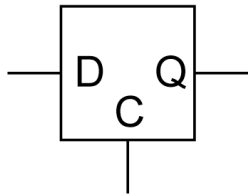


Transistor Circuit for inverting-multiplexor:

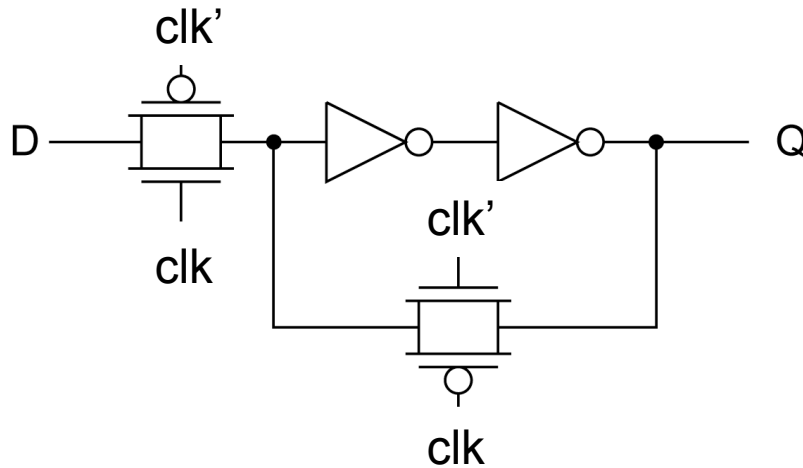


# Latches and Flip-flops

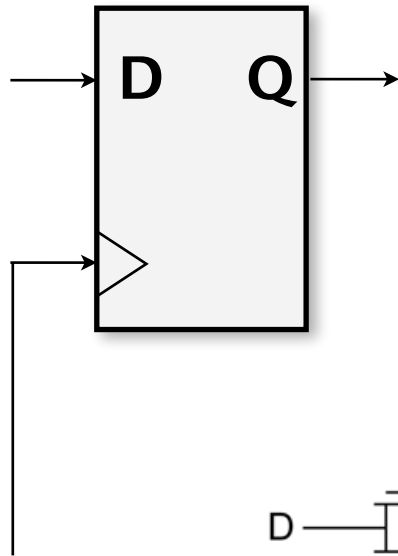
Positive Level-sensitive *latch*:



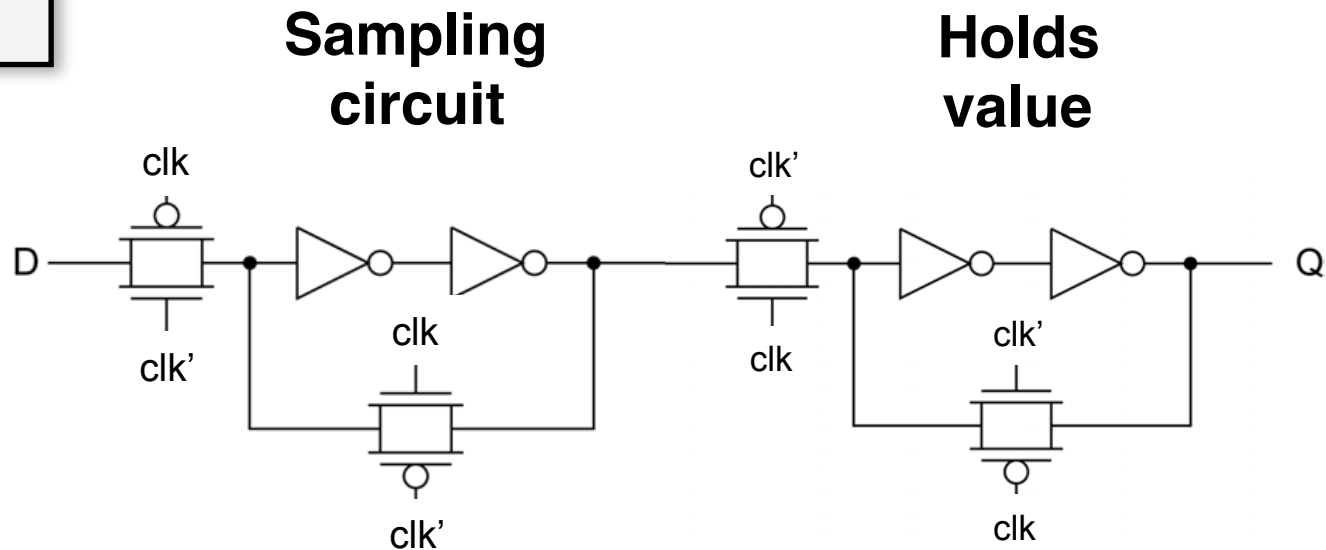
Latch Implementation:



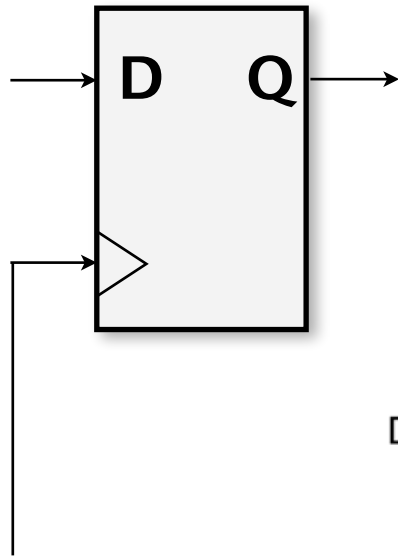
# Positive edge-triggered flip-flop



A flip-flop “samples” right before the edge, and then “holds” value.

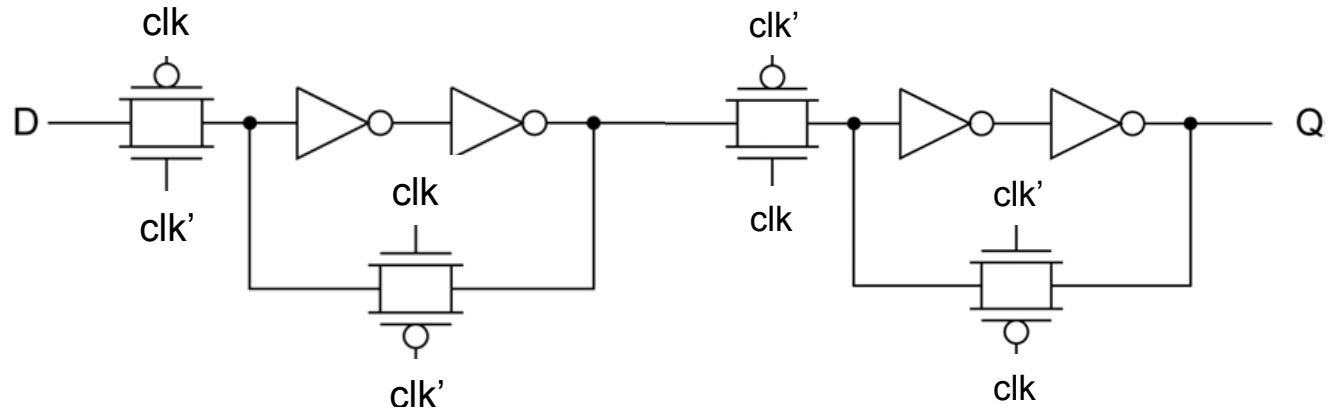


# Sensing: When clock is low

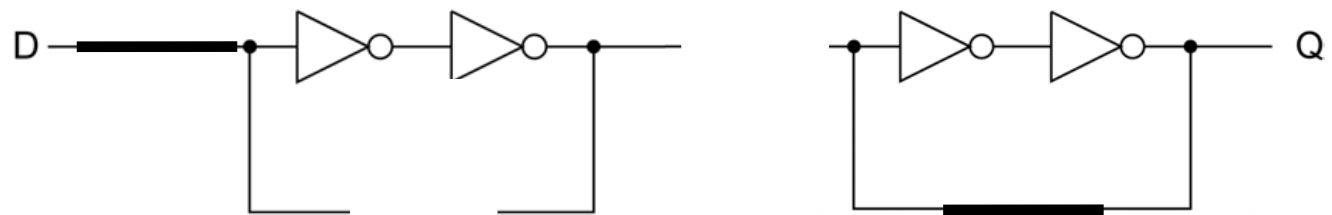


A flip-flop “samples” just before the edge, and then “holds” value.

**Sampling circuit**



$clk = 0$   
 $clk' = 1$



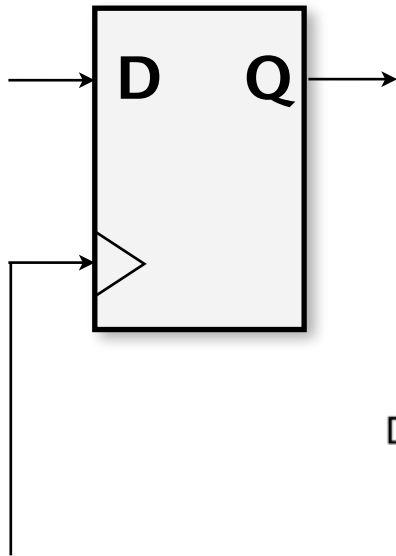
Will capture new value on posedge.

Outputs last value captured.

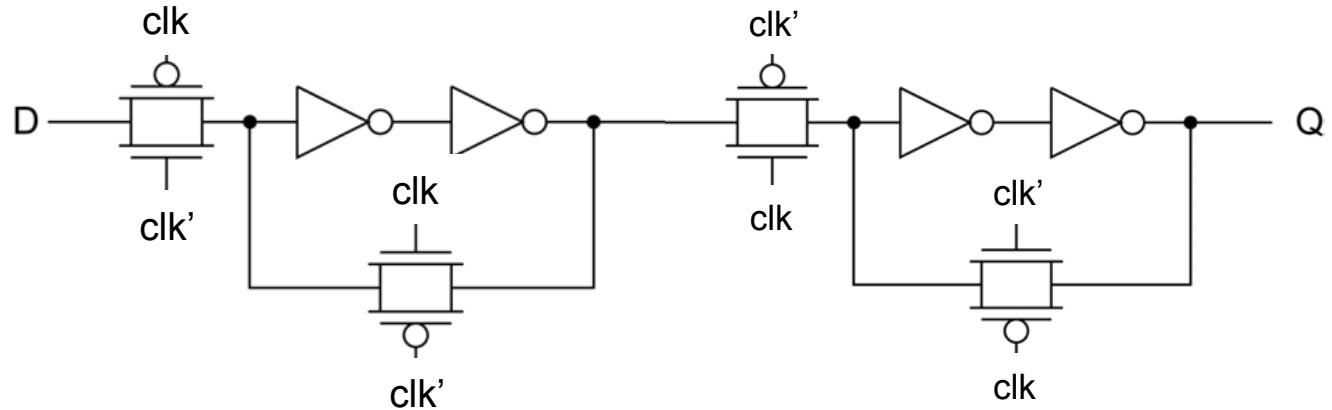


# Capture: When clock goes high

A flip-flop “samples” right before the edge, and then “holds” value.

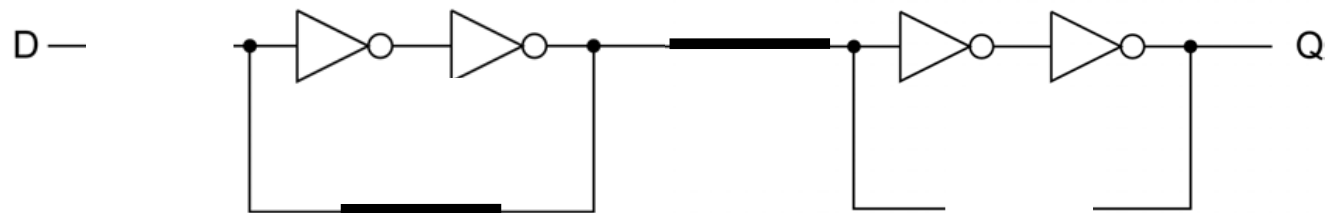


**Sampling circuit**



**Holds value**

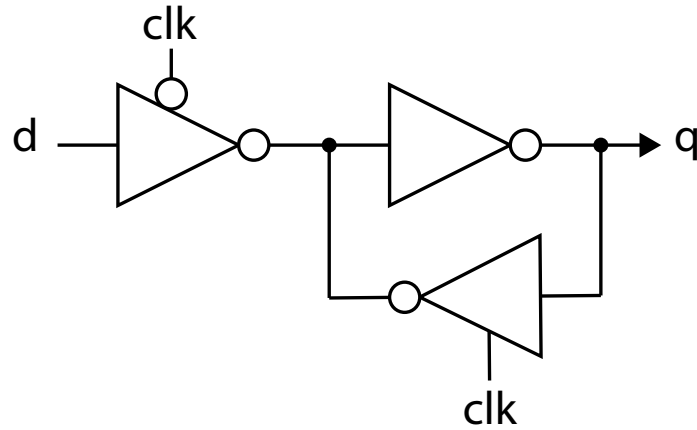
$clk = 1$   
 $clk' = 0$



**Remembers value just captured.**

**Outputs value just captured.**

# Tri-state-Inverter Latch



*Positive Level-sensitive latch:*

- ❑ Commonly used in standard cell flip-flops.
- ❑ More transistors than pass-transistor version, but more robust.
- ❑ Lays out well with modern layout rules.